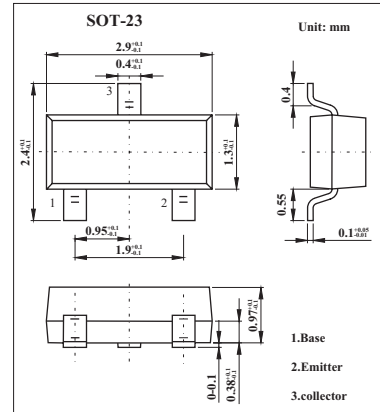
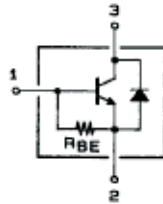


2SD2324

■ **Features**

- Low saturation voltage.
- Contains a diode between collector and emitter.
- Contains a bias resistor between base and emitter.
- Large current capacity.
- Small-sized package facilitating the realization of high-density, small-sized hybrid ICs.



■ **Absolute Maximum Ratings** Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage, With Zener diode (11±3V)	V _{CB0}	20	V
Collector-emitter voltage, With Zener diode (11±3V)	V _{CEO}	15	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	I _c	0.8	A
Collector current (pulse)	I _{cP}	2	A
Collector dissipation	P _c	200	mW
Jumction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ **Electrical Characteristics** Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I _{cBO}	V _{CB} = 15V , I _E = 0			1.0	μA
DC current Gain	h _{FE}	V _{CE} = 2V , I _c = 0.5A	70			
Gain bandwidth product	f _T	V _{CE} = 2V , I _c = 0.5A		150		MHz
Output capacitance	C _{ob}	V _{CB} = 10V , f = 1MHz		15		pF
Collector-emitter saturation voltage	V _{CE(sat)}	I _c = 500mA , I _B = 10mA		0.16	0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _c = 500mA , I _B = 10mA		0.85	1.2	V
Collector-to-base breakdown voltage	V _{(BR)CBO}	I _c = 10μA , I _E = 0	20			V
Collector-to-emitter breakdown voltage	V _{(BR)CEO}	I _c = 10μA , R _{BE} = ∞	20			V
		I _c = 10mA , R _{BE} = ∞	15			
Diode forward voltage	V _F	I _F = 0.5A			1.5	V
Base-emitter resistance	R _{BE}			1		kΩ

■ **Marking**

Marking	BN
---------	----